

New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

HIGH SPEED
Silicon Controlled Rectifier

C384/C385

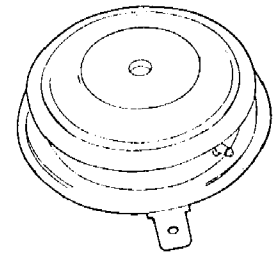
800 Volts

400A RMS

C384 and C385 Silicon Controlled Rectifiers are designed for power switching at high frequencies. These are all-diffused Press-Pak devices, employing the field-proven amplifying gate.

FEATURES:

- Fully Characterized for Operation in Inverter and Chopper Applications.
- High di/dt Ratings.
- High dv/dt Capability with Selections Available.
- Rugged Hermetic Glazed Ceramic Package.



MAXIMUM ALLOWABLE RATINGS

TYPES	REPETITIVE PEAK OFF-STATE VOLTAGE, V_{DRM}^1 $T_J = -40^\circ\text{C to } +125^\circ\text{C}$	REPETITIVE PEAK REVERSE VOLTAGE, V_{RRM}^1 $T_J = -40^\circ\text{C to } +125^\circ\text{C}$	NON-REPETITIVE PEAK REVERSE VOLTAGE, V_{RRM}^1 $T_J = +125^\circ\text{C}$
C384/C385A	100 Volts	100 Volts	200 Volts
C384/C385B	200	200	300
C384/C385C	300	300	400
C384/C385D	400	400	500
C384/C385E	500	500	600
C384/C385M	600	600	720
C385S	700	700	940
C385N	800	800	960

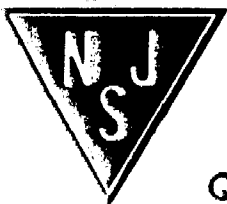
¹ Half sinewave waveform, 10 ms max. pulse width.

Peak One Cycle Surge (Non-Replicative) On-State Current, I_{TSM} (60 Hz)	3500 Amperes
Peak One Cycle Surge (Non-Replicative) On-State Current, I_{TSM} (50 Hz)	3200 Amperes
I^2t (for fusing) for times ≥ 1.5 milliseconds	35,000 (RMS Ampere) ² Seconds
I^2t (for fusing) for times ≥ 8.3 milliseconds	50,000 (RMS Ampere) ² Seconds
Critical Rate-of-Rise of On-State Current, Non-Replicative [†]	800 A/ μ s
Critical Rate-of-Rise of On-State Current, Replicative [†]	500 A/ μ s
Average Gate Power Dissipation, $P_{G(AV)}$	2 Watts
Storage Temperature, T_{stg}	-40°C to +150°C
Operating Temperature, T_J	-40°C to +125°C
Mounting Force Required	.800 Lbs. \pm 10%
	3.56 kN \pm 10%

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

Download from alldatasheet.com



C384/C385

CHARACTERISTICS

TEST	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Repetitive Peak Reverse and Off-State Current	I_{RRM} and I_{DRM}	—	3	10	mA	$T_J = +25^\circ\text{C}$ $V = V_{DRM} = V_{RRM}$
Repetitive Peak Reverse and Off-State Current	I_{RRM} and I_{DRM}	—	15	20	mA	$T_J = 125^\circ\text{C}$ $V = V_{DRM} = V_{RRM}$
Thermal Resistance	$R_{\theta JC}$	—	—	0.19	$^\circ\text{C/Watt}$	Junction-to-Case — One-Side Cooled
		—	—	0.095		Junction-to-Case — Double-Side Cooled
Critical Rate-of-Rise of Off-State Voltage (Higher values may cause device switching)	dv/dt	200	500	—	$\text{V}/\mu\text{sec}$	$T_J = +125^\circ\text{C}$, Gate Open. $V_{DRM} = \text{Rated linear or exponential rising waveform.}$ Exponential $dv/dt = \frac{V_{DRM}}{\tau} (.632)$
Higher minimum dv/dt selections available — consult factory.						
Holding Current	I_H	—	75	500	mA_{dc}	$T_C = +25^\circ\text{C}$, Anode Supply = 24 Vdc, Initial On-State Current = 2.5 Amps.
DC Gate Trigger Current	I_{GT}	—	125	300	mA_{dc}	$T_C = +25^\circ\text{C}$, $V_D = 6\text{Vdc}$, $R_L = 3\text{ Ohms}$
		—	175	500		$T_C = -40^\circ\text{C}$, $V_D = 6\text{Vdc}$, $R_L = 3\text{ Ohms}$
		—	100	250		$T_C = +125^\circ\text{C}$, $V_D = 6\text{Vdc}$, $R_L = 3\text{ Ohms}$
DC Gate Trigger Voltage	V_{GT}	—	—	5.0	Vdc	$T_C = -40^\circ\text{C}$ to 0°C , $V_D = 6\text{Vdc}$, $R_L = 3\text{ Ohms}$
		—	—	3.0		$T_C = 0^\circ\text{C}$ to $+125^\circ\text{C}$, $V_D = 6\text{Vdc}$, $R_L = 3\text{ Ohms}$
		0.15	—	—		$T_C = +125^\circ\text{C}$, V_{DRM} , $R_L = 1000\text{ Ohms}$
Peak On-State Voltage	V_{TM}	—	2.3	2.85	Volts	$T_C = +25^\circ\text{C}$, $I_{TM} = 1500\text{ Amps. Peak.}$ Duty Cycle $\leq .01\%$
Turn-On Delay Time	t_d	—	1	—	μsec	$T_C = +25^\circ\text{C}$, $I_T = 50\text{ Adc}$, V_{DRM} , Gate Supply: 20 Volt-Open Circuit, 20 Ohm, 0.1 $\mu\text{sec. max. rise time.}$
Conventional Circuit Commutated Turn-Off Time (with Reverse Voltage)	t_q	—	—	—	μsec	(1) $T_C = +125^\circ\text{C}$ (2) $I_{TM} = 250\text{ Amps.}$ (3) $V_R = 50\text{ Volts Min.}$ (4) V_{DRM} (Reapplied) (5) Rate-of-Rise of Reapplied Off-State Voltage = $200\text{ V}/\mu\text{sec}$ (linear) (6) Commutation $di/dt = 12.5\text{ Amps}/\mu\text{sec.}$ (7) Duty Cycle $\leq .01\%$ (8) Gate Bias During Turn-Off Interval = 0 Volts, 100 Ohms.
	C385 C384	— —	15 8	20 10		
Conventional Circuit Commutated Turn-Off Time (with Feedback Diode)	$t_q(\text{diode})$	—	—	—	μsec	(1) $T_C = +125^\circ\text{C}$ (2) $I_{TM} = 250\text{ Amps.}$ (3) $V_R = 1\text{ Volt}$ (4) V_{DRM} (Reapplied) (5) Rate-of-Rise of Reapplied Off-State Voltage = $200\text{ V}/\mu\text{sec}$ (linear) (6) Commutation $di/dt = 12.5\text{ Amps}/\mu\text{sec}$ (7) Duty Cycle $\leq .01\%$ (8) Gate Bias During Turn-Off Interval = 0 Volts, 100 Ohms
	C385 C384	— —	20 10	† †		

†Consult factory for maximum turn-off time.